

REMARKS

The Examiner contends that because Li, for example, shows a non-one-hundred percent or non-zero reflectance in Figure 3 at the blue light wavelength, this suggests that there is absorbance of blue light. Even if this were so, it certainly suggests nothing about selective absorbance of blue light. For example in Figure 3, many wavelengths have non-zero and non-one-hundred percent reflectance. Thus, there is nothing selective about blue light absorbance.

In other words, the reflectance characteristics fail to teach selectively absorbing blue light as originally argued. Plainly, a large range of wavelengths would be absorbed according to the Examiner's theory, suggesting that the reference teaches away rather than teaching the claimed invention.

Concerning the comments in paragraph 13 relating to small grain sizes, it was simply pointed out that in order to make the layer blue light absorbent, small grain sizes are achieved in the silicon nitride and oxide layers. The fact that no such teaching is contained in the cited reference suggests that these layers are not selectively blue light absorbent.

Concerning the rejection of claim 25 on the combination of Li in view of Hosokawa, the office action contends the use of a low temperature deposition process to deposit a silver layer is taught by Hosokawa. Of course, the problem is that the substrate in Hosokawa is the glass substrate, which does not present the problems of a silicon substrate. The claim calls for depositing silver on a silicon substrate at a temperature less than 50°C which is nowhere suggested in Hosokawa. In other words, the reason for the low temperature deposition is nowhere explained in Hosokawa and Hosokawa deposits at that temperature on a glass substrate. Therefore, this would not suggest any reason to do so in connection with a silicon substrate.

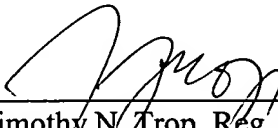
By depositing at low temperature on a silicon substrate the deleterious effects of silver on silicon may be substantially lessened.

No rationale is provided by the reference to deposit at low temperatures on silicon or anywhere else for that matter since no rationale for the choice of temperature is anywhere suggested.

In view of these remarks, the application is now in condition for allowance and the Examiner's prompt action in accordance therewith is respectfully requested.

Respectfully submitted,

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